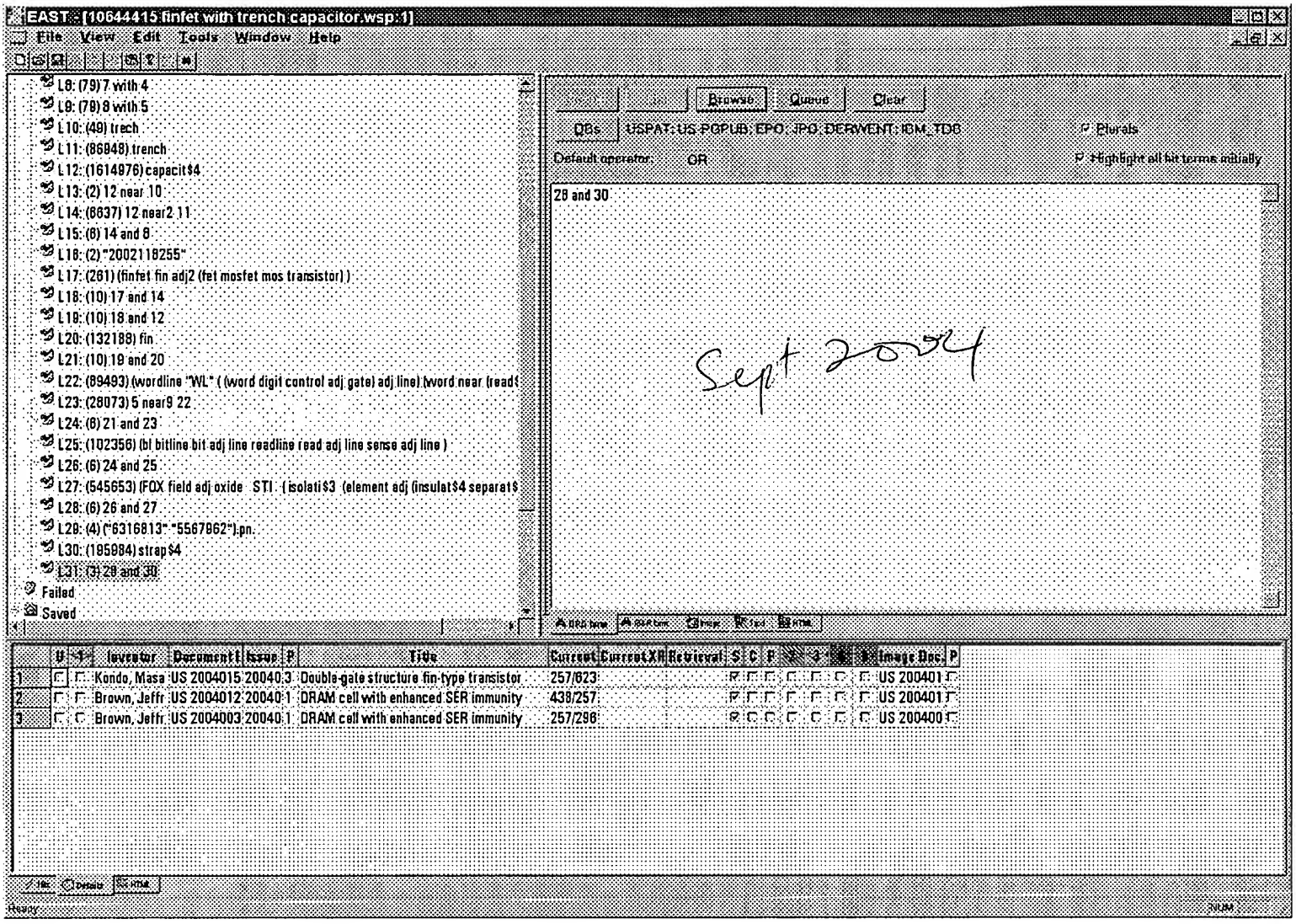
EAST - [10644415 finfet with trench capacitor.wsp: 1]
File View Edit Tools Window Help
L8: (79) 7 with 4
L9: (79) 8 with 5
L10: (49) trech
L11: (86948) trench
L12: (1614876) capacit$4
L13: (2) 12 near 10
L14: (6637) 12 near2 11
L15: (8) 14 and 8
L16: (2) "20021118255"
L17: (261) (finfet fin adj2 (fet mosfet mos transistor))
L18: (10) 17 and 14
L19: (10) 18 and 12
L20: (132188) fin
L21: (10) 19 and 20
L22: (89493) (wordline "WL" ((word digit control adj gate) adj line) (word near (read
L23: (28073) 5 near9 22
L24: (8) 21 and 23
L25: (102356) (bl bitline bit adj line readline read adj line sense adj line)
L26: (6) 24 and 25
L27: (545653) (FOX field adj oxide STI (isolati$3 (element adj (insulat$4 separat$
L28: (6) 26 and 27
L29: (4) ("6316813" "5567862").pn.
L30: (185084) strap$4
L31: (3) 29 and 30
Failed
Saved
Browse
Queue
Clear
DBs
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Plurals
Default operator: OR
Highlight all hit terms initially
29 and 30
Sept 2004
U
Inventor
Document I
Issue
P
Title
Current
CurrentXR
Retrieval
Image Doc.
1 Kondo, Masa US 2004015 20040 3 Double-gate structure fin-type transistor 257/623 US 200401
2 Brown, Jeffr US 2004012 20040 1 DRAM cell with enhanced SER immunity 438/257 US 200401
3 Brown, Jeffr US 2004003 20040 1 DRAM cell with enhanced SER immunity 257/296 US 200400
Details
Ready
NUM